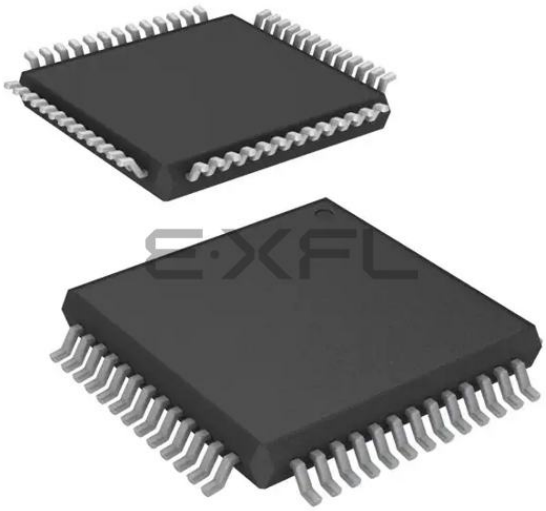

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, Voltage Detect, WDT
Number of I/O	41
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21247snfp-v2

1. Overview

These MCUs are fabricated using a high-performance silicon gate CMOS process, embedding the R8C/Tiny Series CPU core, and are packaged in a 52-pin molded-plastic LQFP or a 64-pin molded-plastic FLGA. It implements sophisticated instructions for a high level of instruction efficiency. With 1 Mbyte of address space, they are capable of executing instructions at high speed.
Furthermore, the R8C/25 Group has on-chip data flash (1 KB x 2 blocks).
The difference between the R8C/24 Group and R8C/25 Group is only the presence or absence of data flash. Their peripheral functions are the same.

1.1 Applications

Electronic household appliances, office equipment, audio equipment, consumer products, etc.

1.2 Performance Overview

Table 1.1 outlines the Functions and Specifications for R8C/24 Group and Table 1.2 outlines the Functions and Specifications for R8C/25 Group.

Table 1.1 Functions and Specifications for R8C/24 Group

Item			Specification
CPU	Number of fundamental instructions		89 instructions
	Minimum instruction execution time		50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 2.2 to 5.5 V)
	Operating mode		Single-chip
	Address space		1 Mbyte
	Memory capacity		Refer to **Table 1.3 Product Information for R8C/24 Group**
Peripheral Functions	Ports		I/O ports: 41 pins, Input port: 3 pins
	LED drive ports		I/O ports: 8 pins
	Timers		Timer RA: 8 bits × 1 channel Timer RB: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer RD: 16 bits × 2 channels (Input capture and output compare circuits) Timer RE: With real-time clock and compare match function
	Serial interfaces		2 channels (UART0, UART1) Clock synchronous serial I/O, UART
	Clock synchronous serial interface		1 channel I²C bus Interface(1) Clock synchronous serial I/O with chip select
	LIN module		Hardware LIN: 1 channel (timer RA, UART0)
	A/D converter		10-bit A/D converter: 1 circuit, 12 channels
	Watchdog timer		15 bits × 1 channel (with prescaler) Reset start selectable
	Interrupts		Internal: 11 sources, External: 5 sources, Software: 4 sources, Priority levels: 7 levels
	Clock	Clock generation circuits	3 circuits • XIN clock generation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has a frequency adjustment function • XCIN clock generation circuit (32 kHz)
			Real-time clock (timer RE)
	Oscillation stop detection function		XIN clock oscillation stop detection function
	Voltage detection circuit		On-chip
	Power-on reset circuit		On-chip
Electrical Characteristics	Supply voltage		VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz) VCC = 2.2 to 5.5 V (f(XIN) = 5 MHz)
	Current consumption		Typ. 10 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 6 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 2.0 μA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage		VCC = 2.7 to 5.5 V
	Programming and erasure endurance		100 times
Operating Ambient Temperature			-20 to 85°C (N version)
			-40 to 85°C (D version)(2)
			-20 to 105°C (Y version)(3)
Package			52-pin molded-plastic LQFP
			64-pin molded-plastic FLGA

NOTES:
1. I²C bus is a trademark of Koninklijke Philips Electronics N. V.
2. Specify the D version if D version functions are to be used.
3. Please contact Renesas Technology sales offices for the Y version.

Table 1.4 Product Information for R8C/25 Group Current of Feb. 2008

Type No.	ROM Capacity		RAM Capacity	Package Type	Remarks
	Program ROM	Data flash			
R5F21254SNFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0052JA-A	N version Blank product
R5F21255SNFP	24 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21256SNFP	32 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21257SNFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0052JA-A	
R5F21258SNFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0052JA-A	
R5F21254SNLG	16 Kbytes	1 Kbyte × 2	1 Kbyte	PTLG0064JA-A	
R5F21256SNLG	32 Kbytes	1 Kbyte × 2	2 Kbytes	PTLG0064JA-A	
R5F21254SDFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0052JA-A	D version Blank product
R5F21255SDFP	24 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21256SDFP	32 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21257SDFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0052JA-A	
R5F21258SDFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0052JA-A	
R5F21254SNXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0052JA-A	N version Factory programming product(1)
R5F21255SNXXXFP	24 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21256SNXXXFP	32 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21257SNXXXFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0052JA-A	
R5F21258SNXXXFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0052JA-A	
R5F21254SNXXXLG	16 Kbytes	1 Kbyte × 2	1 Kbyte	PTLG0064JA-A	
R5F21256SNXXXLG	32 Kbytes	1 Kbyte × 2	2 Kbytes	PTLG0064JA-A	
R5F21254SDXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0052JA-A	D version Factory programming product(1)
R5F21255SDXXXFP	24 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21256SDXXXFP	32 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21257SDXXXFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0052JA-A	
R5F21258SDXXXFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0052JA-A	

NOTE:
1. The user ROM is programmed before shipment.

Pin assignments (top perspective view)

	A	B	C	D	E	F	G	H	
8	3 P3_3/SSI	50 P0_1/AN6	48 P0_3/AN4	46 P6_2	45 P6_0/TREO	NC	36 P6_4	NC	8
7	4 P3_4/SDA/$\overline{\text{SCS}}$	51 P0_0/AN7	49 P0_2/AN5	NC	44 P4_2/VREF	34 P3_0/TRAO	35 P6_5/CLK1	NC	7
6	NC	5 MODE	52 P3_7/SSO	47 P6_1	43 P0_4/AN3	42 P0_5/AN2	NC	33 P3_1/TRBO	6
5	7 P4_4/XCOUT	NC	6 P4_3/XCIN	2 P3_5/SCL/SSCK	37 P6_3	NC	41 P0_6/AN1	38 P0_7/AN0	5
4	13 P2_7/TRDIOD1	12 VCC/AVCC	NC	9 XOUT/P4_7(1)	8 $\overline{\text{RESET}}$	32 P1_0/$\overline{\text{KI0}}$/AN8	31 P1_1/$\overline{\text{KI1}}$/AN9	NC	4
3	NC	10 VSS/AVSS	16 P2_4/TRDIOA1	19 P2_1/TRDIOB0	23 P1_5/RXD0/(TRAIO)/($\overline{\text{INT1}}$)(2)	NC	NC	30 P1_2/$\overline{\text{KI2}}$/AN10	3
2	NC	11 XIN/P4_6	17 P2_3/TRDIOD0	20 P2_0/TRDIOA0/TRDCLK	NC	24 P1_4/TXD0	28 P6_6/$\overline{\text{INT2}}$/TXD1	NC	2
1	14 P2_6/TRDIOC1	15 P2_5/TRDIOB1	18 P2_2/TRDIOC0	21 P1_7/TRAIO/$\overline{\text{INT1}}$	22 P1_6/CLK0	25 P1_3/$\overline{\text{KI3}}$/AN11	27 P4_5/$\overline{\text{INT0}}$	29 P6_7/$\overline{\text{INT3}}$/RXD1	1
	A	B	C	D	E	F	G	H	

Package: PTLG0064JA-A(64F0G)
0.65 mm pin pitch, 6 mm square body

NOTES:
1. P4_7 is an input-only port.
2. Can be assigned to the pin in parentheses by a program.
3. In the figure, the numbers in circles are the pin numbers of the 52-pin LQFP package (PLQP0052JA-A).
   NC: Non-Connection

R5F21244S
NLG
JAPAN

Pin assignments (top view)

Figure 1.5 PTLG0064JA-A Package Pin Assignments

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 and as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the start address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP, and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/24 Group	100(3)	–	–	times
		R8C/25 Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		-20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. -40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

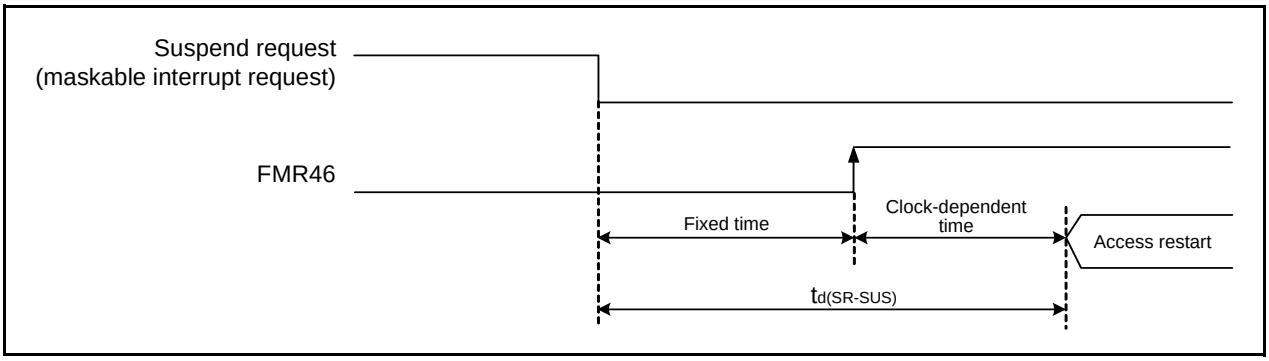


Figure 5.2 Time delay until Suspend

Table 5.6 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level		2.2	2.3	2.4	V
–	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	–	0.9	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	300	µs
Vccmin	MCU operating voltage minimum value		2.2	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.

Table 5.7 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level		2.70	2.85	3.00	V
–	Voltage monitor 1 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.8 Voltage Detection 2 Circuit Electrical Characteristics

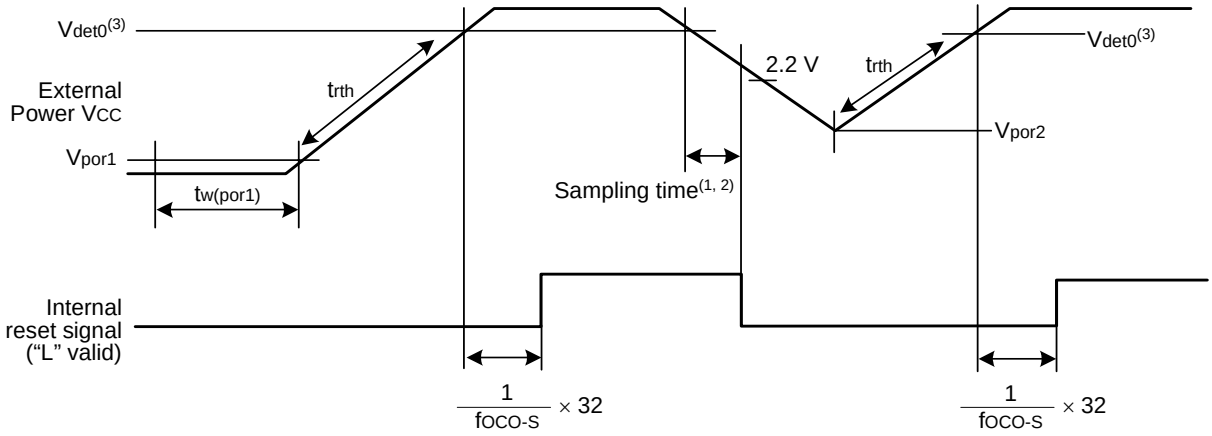
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level		3.3	3.6	3.9	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.9 Power-on Reset Circuit, Voltage Monitor 0 Reset Electrical Characteristics(3)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage(4)		–	–	0.1	V
V_{por2}	Power-on reset or voltage monitor 0 reset valid voltage		0	–	V_{det0}	V
t_{rth}	External power V_{CC} rise gradient(2)		20	–	–	mV/msec

NOTES:
1. The measurement condition is T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. This condition (external power V_{CC} rise gradient) does not apply if $V_{CC} \geq 1.0$ V.
3. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVD0ON bit in the OFS register to 0, the VW0C0 and VW0C6 bits in the VW0C register to 1 respectively, and the VCA25 bit in the VCA2 register to 1.
4. $t_{w(por1)}$ indicates the duration the external power V_{CC} must be held below the effective voltage (V_{por1}) to enable a power on reset. When turning on the power for the first time, maintain $t_{w(por1)}$ for 30 s or more if -20°C ≤ T_{opr} ≤ 85°C, maintain $t_{w(por1)}$ for 3,000 s or more if -40°C ≤ T_{opr} < -20°C.



NOTES:
1. When using the voltage monitor 0 digital filter, ensure that the voltage is within the MCU operation voltage range (2.2 V or above) during the sampling time.
2. The sampling clock can be selected. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.
3. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.

Figure 5.3 Power-on Reset Circuit Electrical Characteristics

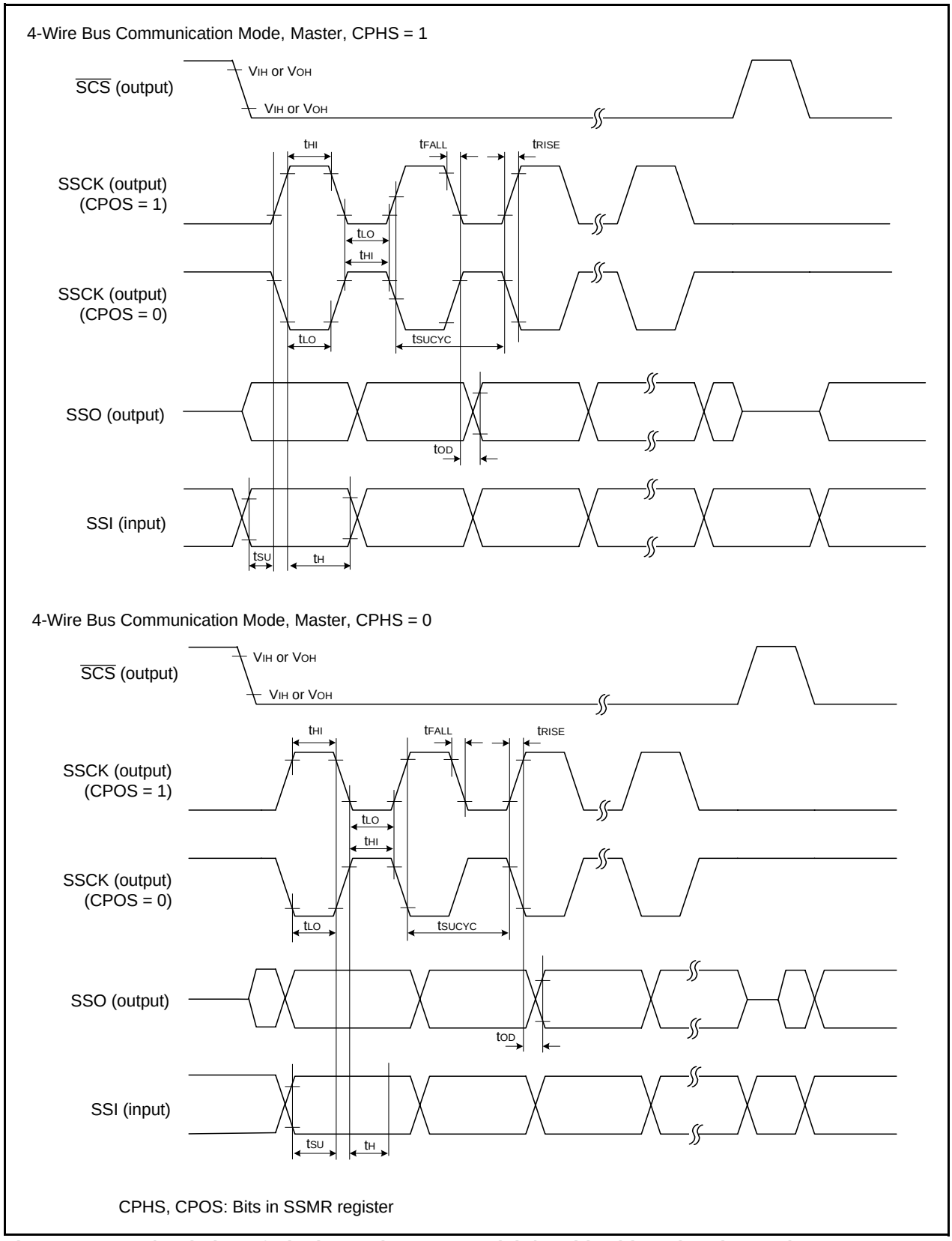


Figure 5.4 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)

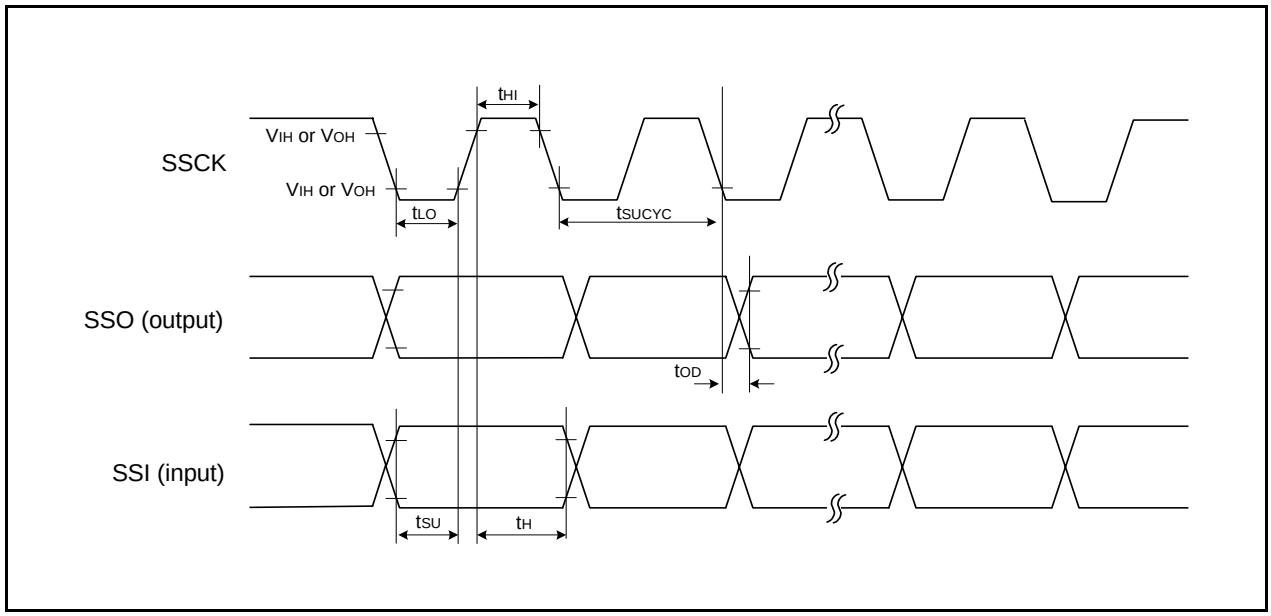


Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Timing Requirements
(Unless Otherwise Specified: Vcc = 5 V, Vss = 0 V at Topr = 25°C) [Vcc = 5 V]

Table 5.18 XIN Input, XCIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

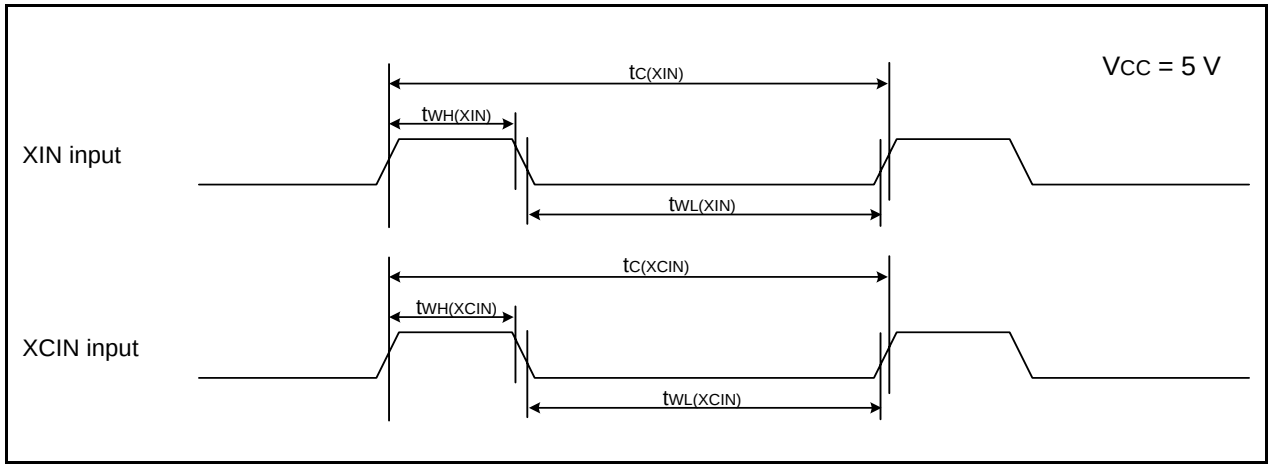


Figure 5.8 XIN Input and XCIN Input Timing Diagram when Vcc = 5 V

Table 5.19 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

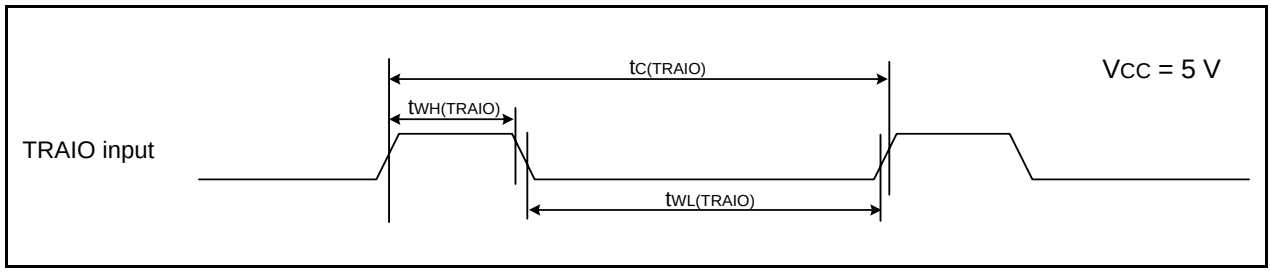


Figure 5.9 TRAIO Input Timing Diagram when Vcc = 5 V

Table 5.22 Electrical Characteristics (3) [Vcc = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P2_0 to P2_7, XOUT	I_{OH} = -1 mA		Vcc - 0.5	–	Vcc	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OH} = -5 mA	Vcc - 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = -1 mA	Vcc - 0.5	–	Vcc	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	Vcc - 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = -50 µA	Vcc - 0.5	–	Vcc	V
V_{OL}	Output “L” voltage	Except P2_0 to P2_7, XOUT	I_{OL} = 1 mA		–	–	0.5	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OL} = 5 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, Vcc = 3V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, Vcc = 3V		–	–	-4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, Vcc = 3V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. Vcc =2.7 to 3.3 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

Timing requirements
(Unless Otherwise Specified: V_{CC} = 3 V, V_{SS} = 0 V at Topr = 25°C) [V_{CC} = 3 V]

Table 5.24 XIN Input, XCIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	100	–	ns
$t_{WH(XIN)}$	XIN input “H” width	40	–	ns
$t_{WL(XIN)}$	XIN input “L” width	40	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

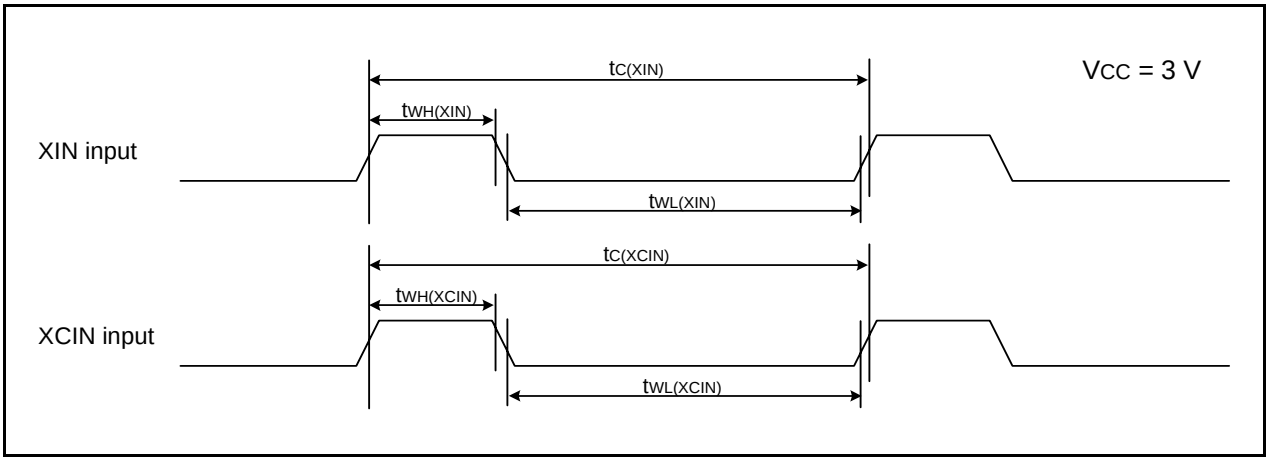


Figure 5.12 XIN Input and XCIN Input Timing Diagram when V_{CC} = 3 V

Table 5.25 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	–	ns

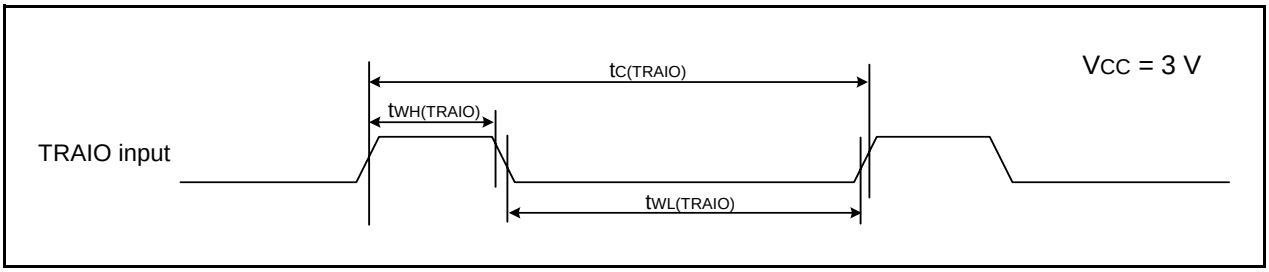


Figure 5.13 TRAIO Input Timing Diagram when V_{CC} = 3 V

Table 5.29 Electrical Characteristics (6) [Vcc = 2.2 V]
(Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.2 to 2.7 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	100	230	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	100	230	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	25	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	22	60	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	20	55	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.0	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	1.8	–	µA
		Increase during A/D converter operation	Without sample & hold	–	0.4	–	mA
			With sample & hold	–	0.3	–	mA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.7	3.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.1	–	µA

Timing requirements
(Unless Otherwise Specified: V_{CC} = 2.2 V, V_{SS} = 0 V at Topr = 25°C) [V_{CC} = 2.2 V]

Table 5.30 XIN Input, XCIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	200	–	ns
$t_{WH(XIN)}$	XIN input “H” width	90	–	ns
$t_{WL(XIN)}$	XIN input “L” width	90	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

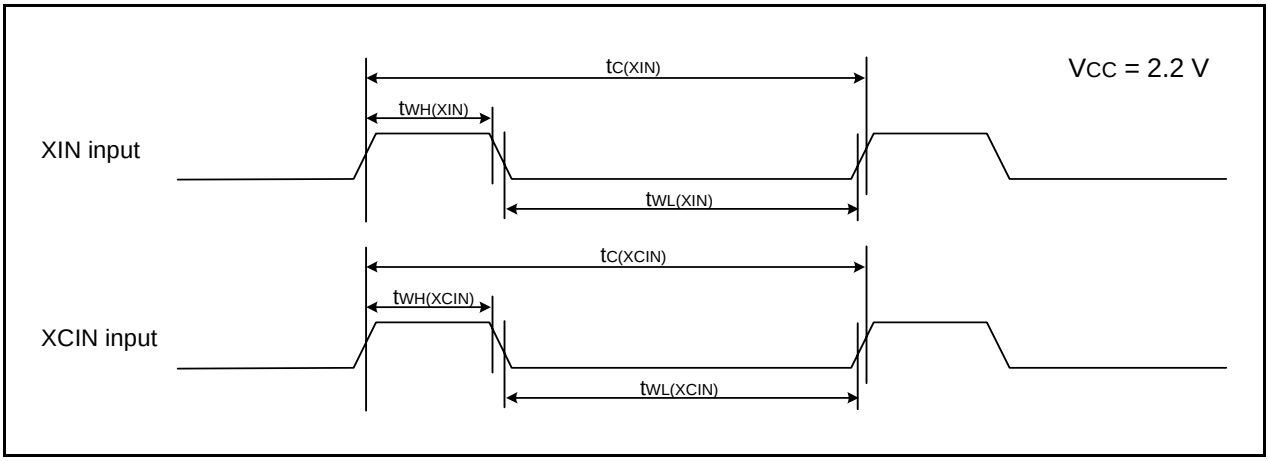


Figure 5.16 XIN Input and XCIN Input Timing Diagram when V_{CC} = 2.2 V

Table 5.31 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	500	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	200	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	200	–	ns

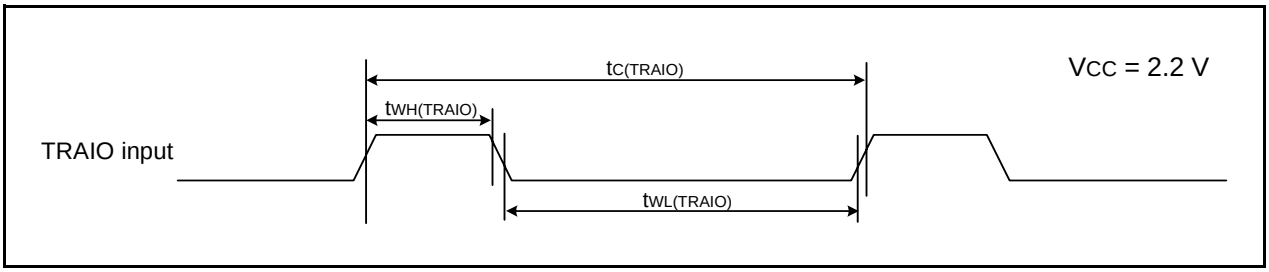


Figure 5.17 TRAIO Input Timing Diagram when V_{CC} = 2.2 V

Table 5.32 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	800	–	ns
$t_{W(CKH)}$	CLKi input “H” width	400	–	ns
$t_{W(CKL)}$	CLKi input “L” width	400	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	200	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	150	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 1

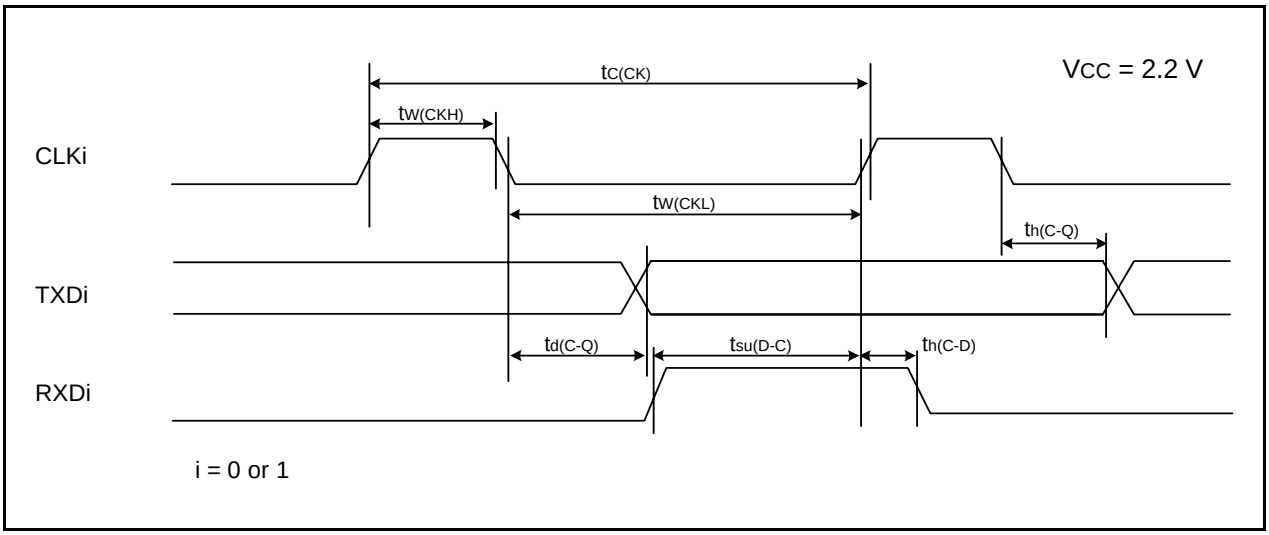


Figure 5.18 Serial Interface Timing Diagram when VCC = 2.2 V

Table 5.33 External Interrupt $\overline{INTi}$ (i = 0 to 3) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INT0}$ input “H” width	1000(1)	–	ns
$t_{W(INL)}$	$\overline{INT0}$ input “L” width	1000(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

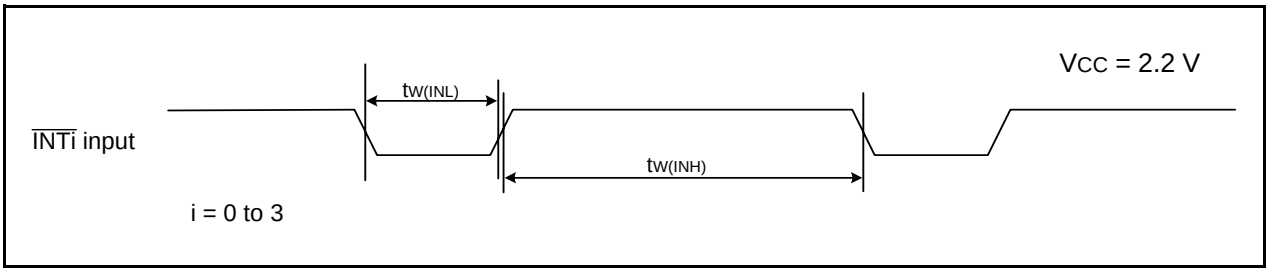


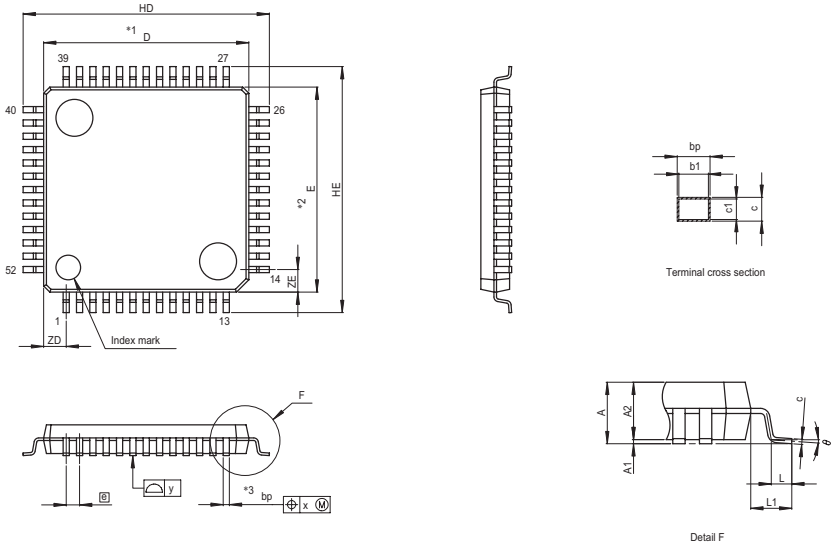
Figure 5.19 External Interrupt $\overline{INTi}$ Input Timing Diagram when VCC = 2.2 V

Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Technology website.

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP52-10x10-0.65	PLQP0052JA-A	52P6A-A	0.3g

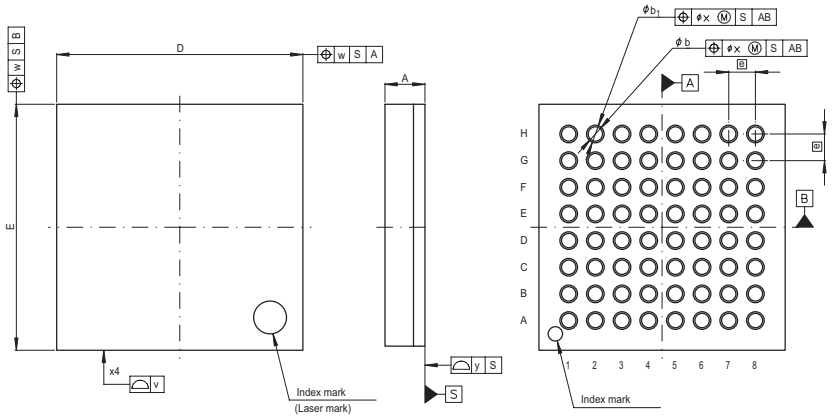
Under development



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A_2	—	1.4	—
H_D	11.8	12.0	12.2
H_E	11.8	12.0	12.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.27	0.32	0.37
b_1	—	0.30	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.65	—
x	—	—	0.13
y	—	—	0.10
Z_D	—	1.1	—
Z_E	—	1.1	—
L	0.35	0.5	0.65
L_1	—	1.0	—

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-TFLGA64-6x6-0.65	PTLG0064JA-A	64F0G	0.07g



Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	6.0	—
E	—	6.0	—
v	—	—	0.15
w	—	—	0.20
A	—	—	1.05
e	—	0.65	—
b	0.31	0.35	0.39
b_1	0.39	0.43	0.47
x	—	—	0.08
y	—	—	0.10

REVISION HISTORY	R8C/24 Group, R8C/25 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.01	Sep 17, 2004	-	First Edition issued
0.02	Dec 10, 2004	All pages	Part Number revised. R8C/26 → R8C/24, R8C/27 → R8C/25
		2, 3	Table 1.1 R8C/24 Group Performance, Table 1.2 R8C/25 Group Performance - Serial Interface: I^2C Bus Interface and Chip-select clock synchronous (SSU) added. - LIN Module added. - Interrupt: Internal factors revised; 10 → 11 - Note on Operating Ambient Temperature added.
		4	Figure 1.1 Block Diagram - LIN Module added. - Chip-select clock synchronous (SSU) is added to I^2C Bus Interface.
		5, 6	Table 1.3 Product Information of R8C/24 Group, Table 1.4 Product Information of R8C/25 Group Date and Development state revised.
		7	Figure 1.4 Pin Assignment P3_5/SCL → P3_5/SCL/SSCK, P3_3 → P3_3/SSI, P3_4/SDA → P3_4/SDA/SCS, P3_7 → P3_7/SSO, VSS/AVSS → VSS, XIN/P4_6 → P4_6/XIN, VCC/AVSS → VCC 12pin P1_7/TRAIO/INT1 to 22pin P1_0/KI0/AN8 → 20pin P1_7/TRAIO/INT1 to 30pin P1_0/KI0/AN8
		8	Table 1.5 Pin Description - Analog Power Supply Input eliminated. - SSU added.
		9	Table 1.6 Pin Name Information by Pin Number added.
		15	Table 4.1 SFR Information (1) - 0031h: Voltage Detection Register 1 → Voltage Detection A Register 1 - 0032h: Voltage Detection Register 1 → Voltage Detection A Register 2 01000001b → 00100001b (Note 4) - 0036h: "(3), 01000001b (4)" eliminated. - 0038h: Voltage Monitor 0 Control Register (2), VW0C, 00001000b (3), 01000001b (4) added.
		16	Table 4.2 SFR Information (2) - 0048h: Timer RD0 Interrupt Control Register, RD0IC, XXXXX000b added. - 0049h: Timer RD Interrupt Control Register, RDIC → Timer RD1 Interrupt Control Register, RD1IC - 004Fh: IIC Interrupt Control Register, IIC → IIC/SSU Interrupt Control Register, IIC2IC
		19	Table 4.5 SFR Information (3) - 0106h: LIN Control Register, LINCR, 00h added. -0107h: LIN Status Register, LINST, 00h added.

Rev.	Date	Description	
		Page	Summary
0.30	Sep 01, 2005	7	Figure 1.4 Pin Assignment • Pin name revised; VSS → VSS/AVSS, VCC → VCC/AVCC, P1_5/RXD0/(TRAIO)/($\overline{\text{INT1}}$) → P1_5/RXD0/(TRAIO)/($\overline{\text{INT1}}$)(2), P6_6/$\overline{\text{INT2}}$/(TXD1) → P6_6/$\overline{\text{INT2}}$/TXD1, P6_7/$\overline{\text{INT3}}$/(RXD1) → P6_7/$\overline{\text{INT3}}$/RXD1, P6_5 → P6_5/CLK1 • NOTE2 added
		8	Table 1.5 Pin Description • Analog Power Supply Input: line added • $\overline{\text{INT}}$ Interrupt Input: "$\overline{\text{INT0}}$ Timer RD input pins. $\overline{\text{INT1}}$ Timer RA input pins." added • Serial Interface: "CLK1" added • "I2C Bus Interface (IIC)" → "I2C Bus Interface" • "SSU" → "Clock Synchronous Serial I/O with Chip Select"
		9	Table 1.6 Pin Name Information by Pin Number revised • Pin Number 10: "VSS" → "VSS/AVSS" • Pin Number 12: "$\overline{\text{VCC}}$" → "VCC/AVCC" • Pin Number 27: "$\overline{\text{INT0}}$" added • Pin Number 28: "(TXD1)" → "TXD1" • Pin Number 29: "(RXD1)" → "RXD1" • Pin Number 35: "CLK1" added
		15	Tabel 4.1 SFR Information(1) revised: • 0012h: X0h → 00h • 0013h: XXXXXX00b → 00h • 0016h: X0h → 00h • 0036h: Voltage Monitor 1 Control Register(2) → Voltage Monitor 1 Control Register(5) • 0038h: 00001000b(3), 01000001b(4) → 0000X000b(3), 0100X001b(4) • NOTES2, 5: "the voltage monitor 1 reset" added • NOTE3: "voltage monitor 1 reset" → "voltage monitor 0 reset"
		16	Tabel 4.2 SFR Information(2) revised: • 0048h: RD0IC → TRD0IC • 0049h: RD1IC → TRD1IC • 004Ah: REIC → TREIC • 004Fh: SSU/IIC Interrupt Control Register, IIC2AIC → SSU/IIC Interrupt Control Register(2), SSUAIC/IIC2AIC • 0056h: RAIC → TRAIC • 0058h: RBIC → TRBIC • NOTE2 added
		17	Tabel 4.3 SFR Information(3) revised: • 00BCh: 00h → 00h/0000X000b
		18	Tabel 4.4 SFR Information(4) revised: • 00D6h: 00000XXXb → 00h • 00F5h: UART1 Function Select Register, U1SR, XXh added